2SK3203(L), 2SK3203(S)

Silicon N Channel MOS FET
High Speed Power Switching

HITACHI

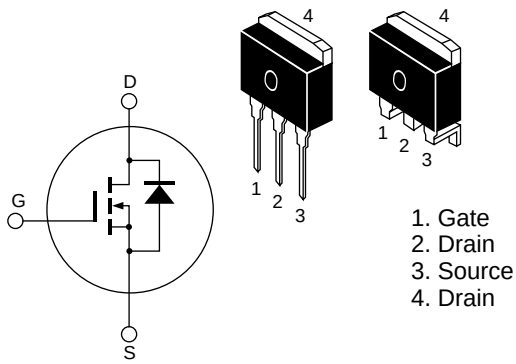
ADE-208-1384A (Z)
2nd. Edition
Jan. 2001

Features

- Low on-resistance
  $R_{DS(on)}$ =11m typ.
- Low drive current
- 5V gate drive device can be driven from 5V source

Outline

LDPAK



1. Gate
2. Drain
3. Source
4. Drain

Hitachi semiconductor

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	30	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	45	A
Drain peak current	$I_{D(pulse)}$*[1]	180	A
Body-drain diode reverse drain current	I_{DR}	45	A
Channel dissipation	Pch*[2]	50	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	–55 to +150	°C

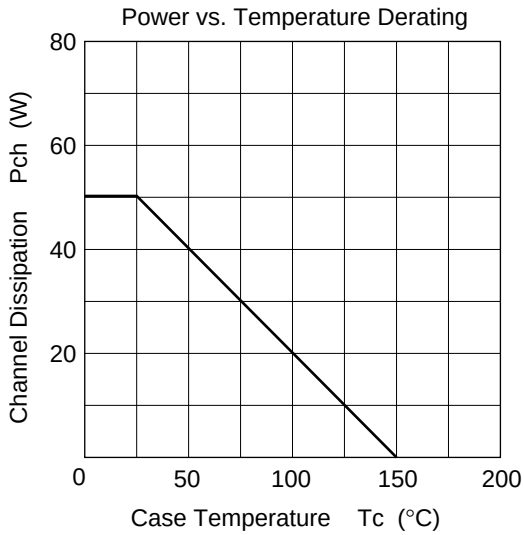
Note: 1. PW ≤ 10µs, duty cycle ≤ 1 %
2. Value at Tc = 25°C
3. Value at Tch = 25°C, Rg ≥ 50Ω

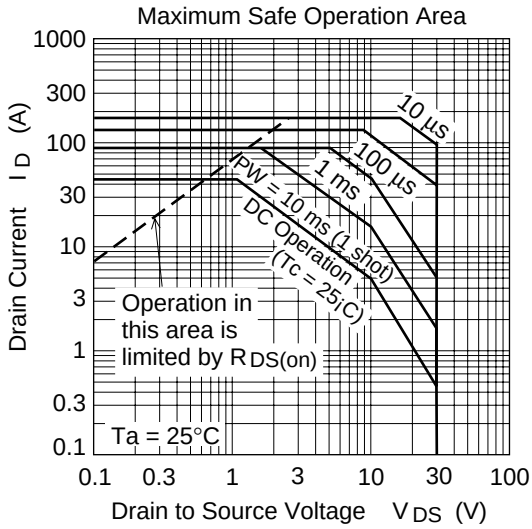
Electrical Characteristics (Ta = 25°C)

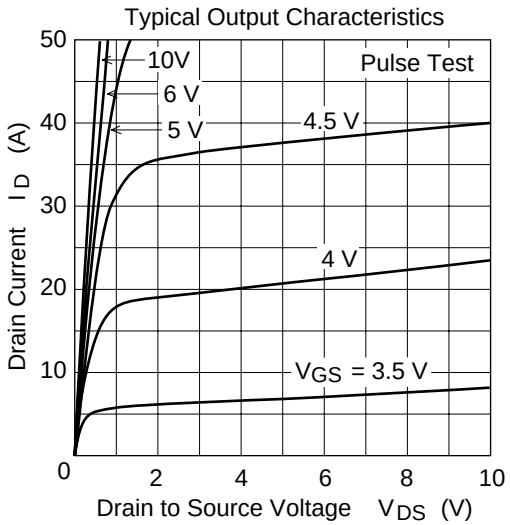
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	30	—	—	V	I_D = 10mA, V_{GS} = 0
Gate to source leak current	I_{GSS}	—	—	±0.1	µA	V_{GS} = ±20V, V_{DS} = 0
Zero gate voltege drain current	I_{DSS}	—	—	10	µA	V_{DS} = 30 V, V_{GS} = 0
Gate to source cutoff voltage	$V_{GS(off)}$	1.5	—	3.0	V	I_D = 1mA, V_{DS} = 10V*[1]
Static drain to source on state	$R_{DS(on)}$	—	11	14	mΩ	I_D = 20A, V_{GS} = 10V*[1]
resistance		—	18	28	mΩ	I_D = 20A, V_{GS} = 5V*[1]
Forward transfer admittance	$\|y_{fs}\|$	13	22	—	S	I_D = 20A, V_{DS} = 10V*[1]
Input capacitance	Ciss	—	1200	—	pF	V_{DS} = 10V
Output capacitance	Coss	—	380	—	pF	V_{GS} = 0
Reverse transfer capacitance	Crss	—	200	—	pF	f = 1MHz
Total gate charge	Qg	—	23	—	nc	V_{DD} = 10V
Gate to source charge	Qgs	—	4.0	—	nc	V_{GS} = 10V
Gate to drain charge	Qgd	—	7.0	—	nc	I_D = 45A
Turn-on delay time	$t_{d(on)}$	—	17	—	ns	V_{GS} = 10V, I_D = 20A
Rise time	t_r	—	300	—	ns	R_L = 0.5Ω
Turn-off delay time	$t_{d(off)}$	—	85	—	ns	
Fall time	t_f	—	65	—	ns	
Body–drain diode forward voltage	V_{DF}	—	1.15	—	V	I_F = 45A, V_{GS} = 0
Body–drain diode reverse recovery time	t_{rr}	—	60	—	ns	I_F =45A, V_{GS} = 0 diF/ dt =20A/µs

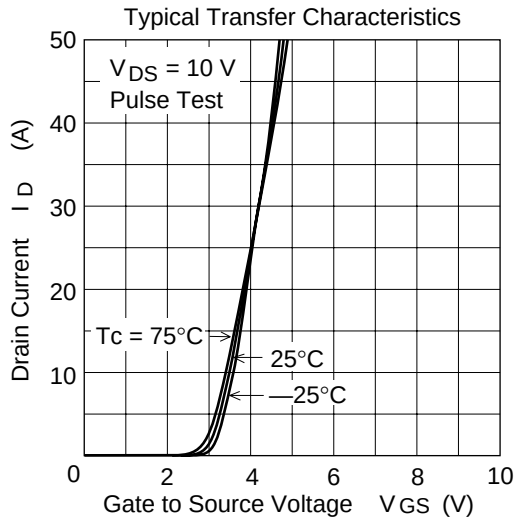
Note: 1. Pulse test

Main Characteristics

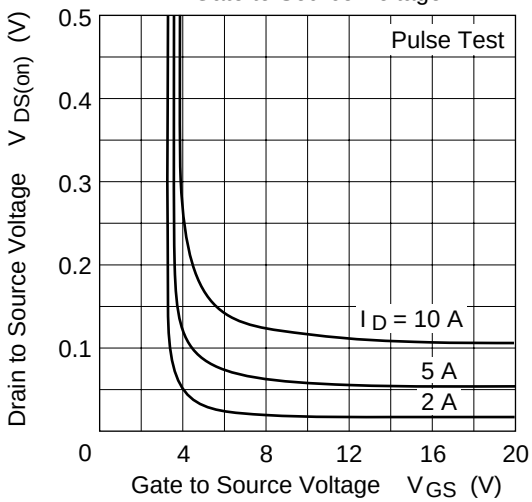




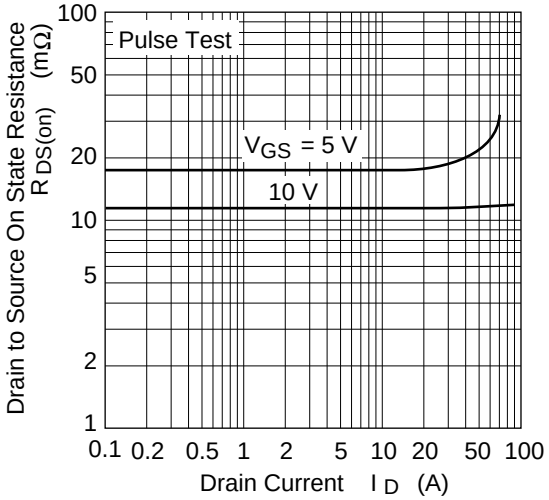




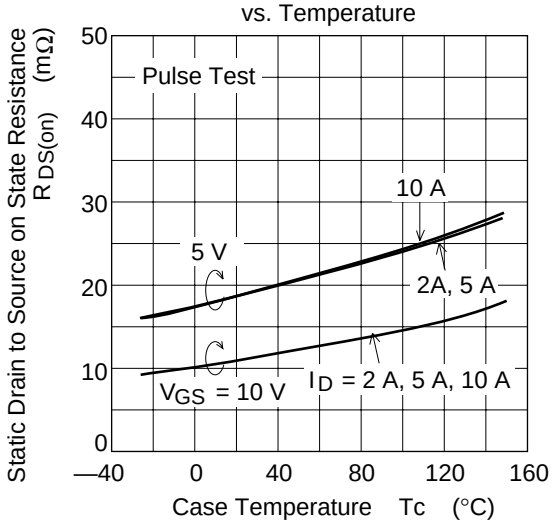
Drain to Source Saturation Voltage vs. Gate to Source Voltage



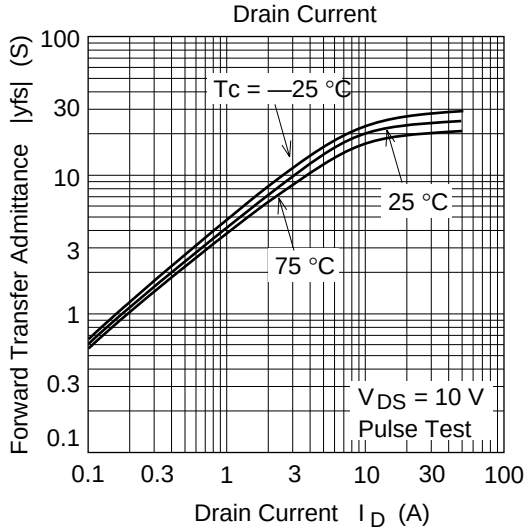
Static Drain to Source on State Resistance vs. Drain Current



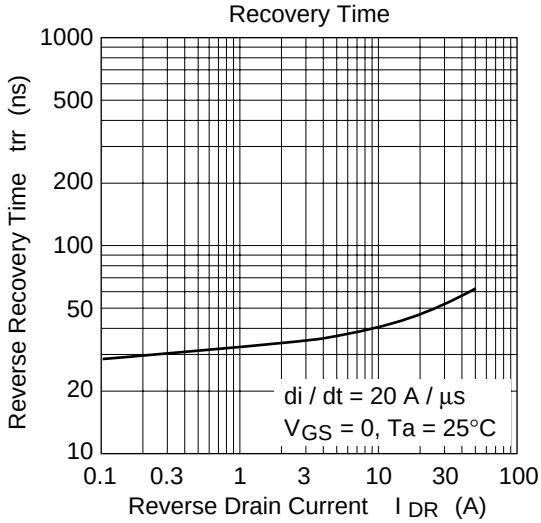
Static Drain to Source on State Resistance vs. Temperature



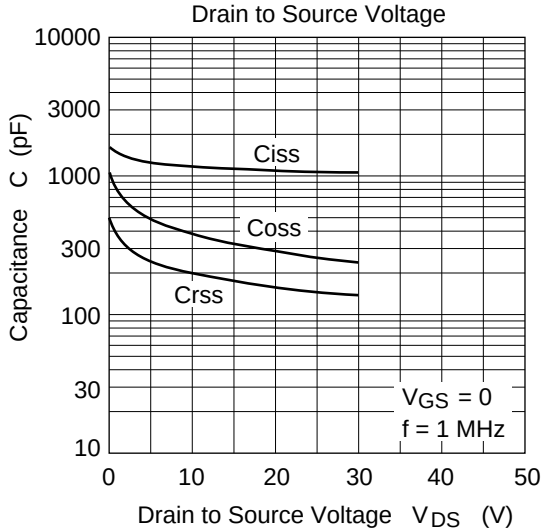
Forward Transfer Admittance vs. Drain Current



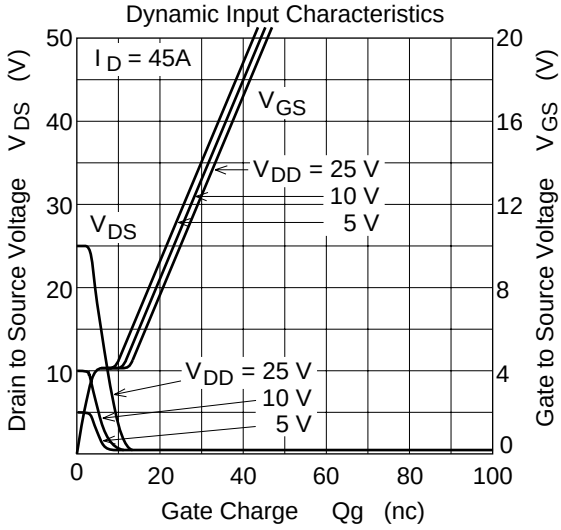
Body—Drain Diode Reverse Recovery Time



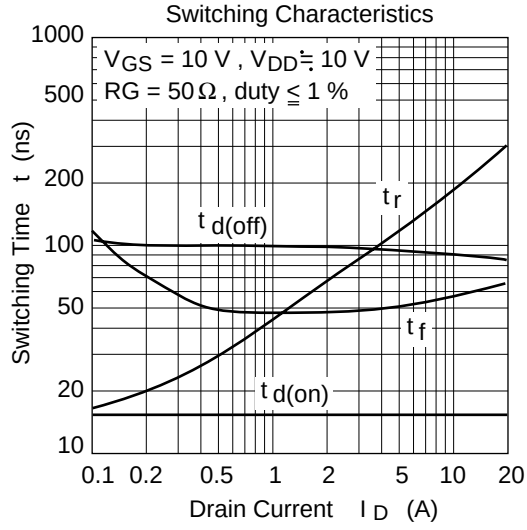
Typical Capacitance vs. Drain to Source Voltage

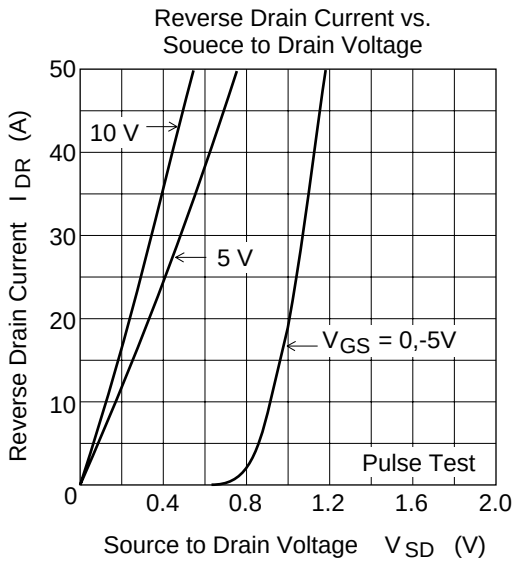


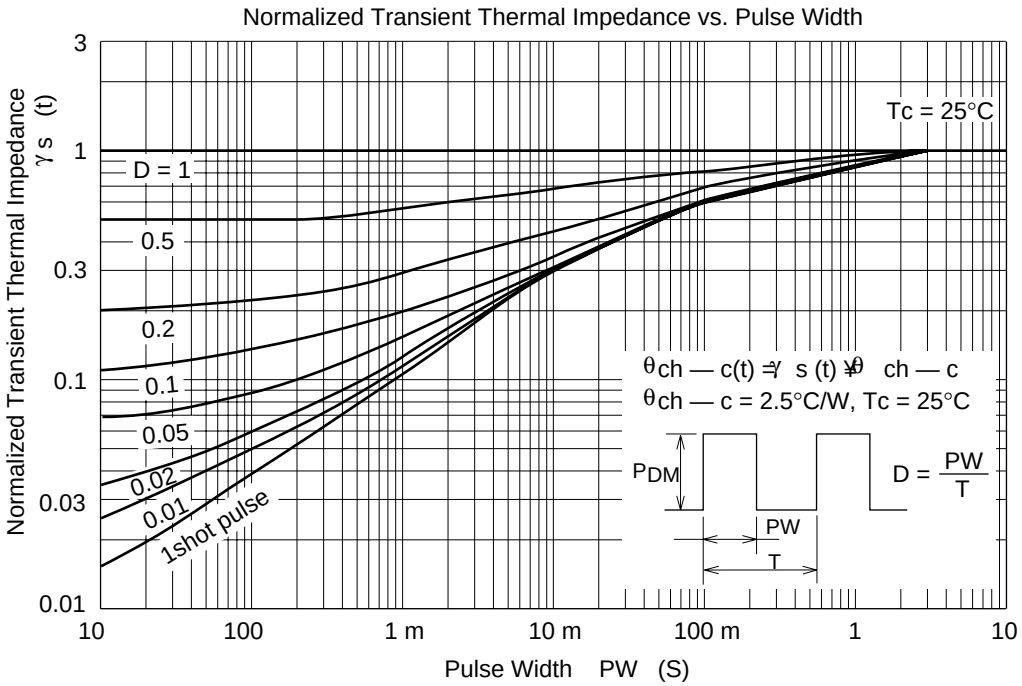
Dynamic Input Characteristics



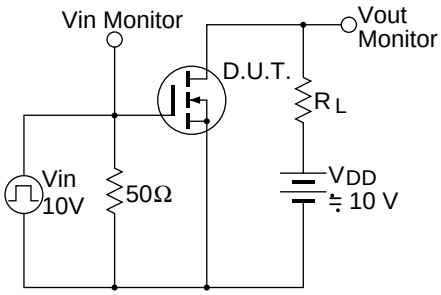
Switching Characteristics



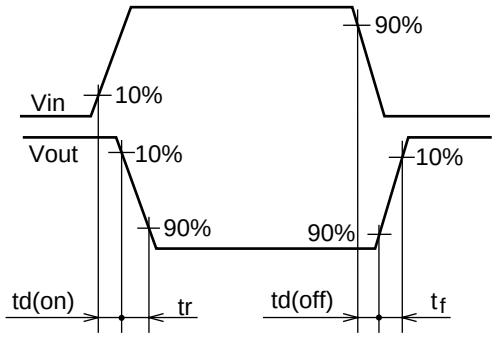

Reverse Drain Current vs.
Souece to Drain Voltage
Reverse Drain Current I DR (A)
50
40
30
20
10
0
10 V
5 V
VGS = 0,-5V
Pulse Test
0.4
0.8
1.2
1.6
2.0
Source to Drain Voltage V SD (V)


Normalized Transient Thermal Impedance vs. Pulse Width
Normalized Transient Thermal Impedance γs (t)
3
1
0.3
0.1
0.03
0.01
Tc = 25°C
D = 1
0.5
0.2
0.1
0.05
0.02
0.01
1shot pulse
θch — c(t) = γs (t) × θch — c
θch — c = 2.5°C/W, Tc = 25°C
PDM
D = PW / T
PW
T
10
100
1 m
10 m
100 m
1
10
Pulse Width PW (S)

Switching Time Test Circuit



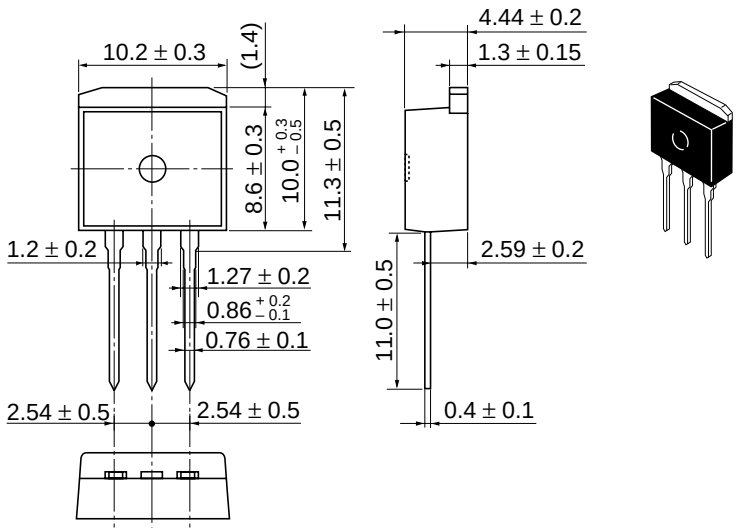
Switching Time Waveform



Package Dimensions

As of January, 2001

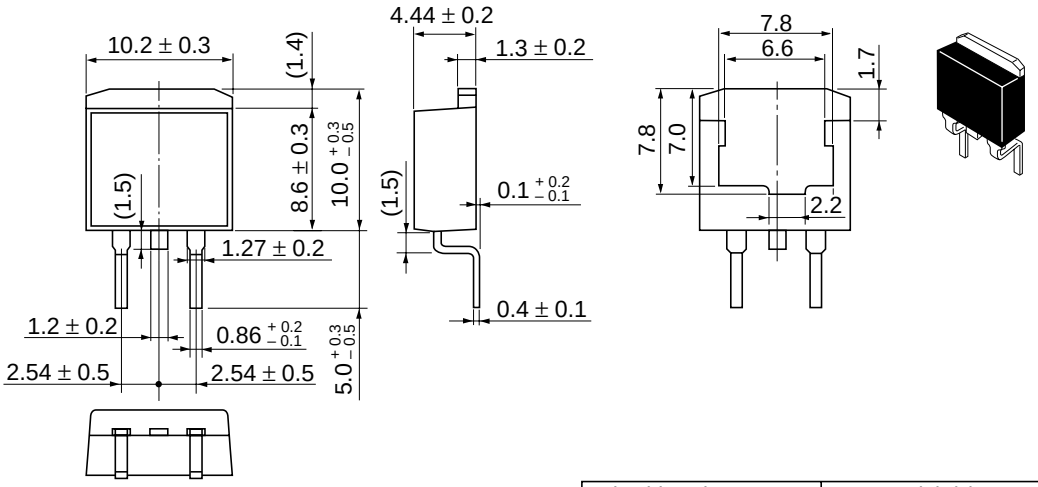
Unit: mm



Hitachi Code	LDPAK (L)
JEDEC	—
EIAJ	—
Mass (reference value)	1.4 g

As of January, 2001

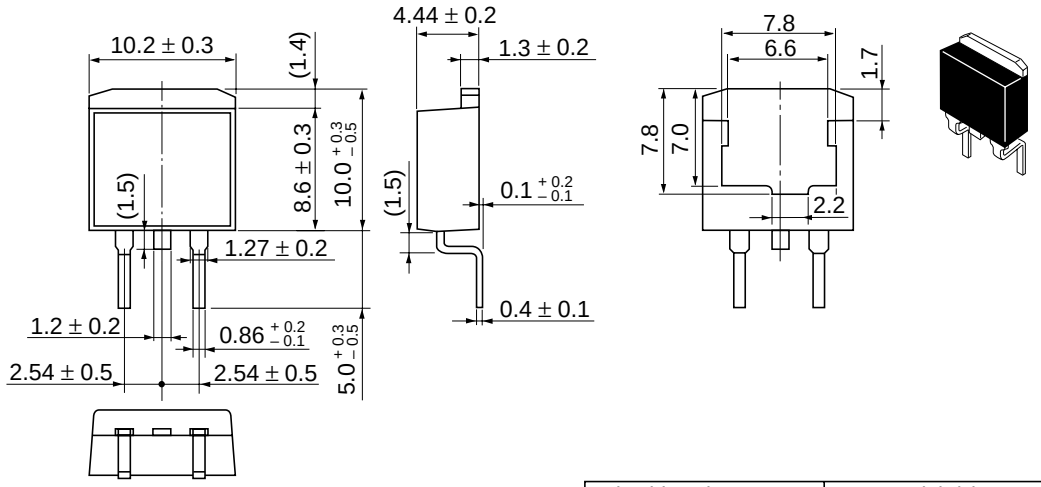
Unit: mm



Hitachi Code	LDPAK (S)-(2)
JEDEC	—
EIAJ	—
Mass (reference value)	1.35 g

As of January, 2001

Unit: mm



Hitachi Code	LDPAK (S)-(2)
JEDEC	—
EIAJ	—
Mass (reference value)	1.35 g

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